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Kind regards,

Team Nexperia



# PMV45EN2

30 V, N-channel Trench MOSFET

10 January 2017

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- Enhanced power dissipation capability of 1115 mW

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

## 4. Quick reference data

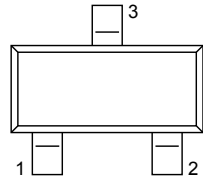
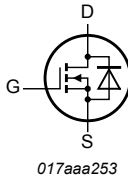
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	-	30	V
$V_{GS}$	gate-source voltage		-20	-	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}; t \leq 5\text{ s}$	[1]	-	5.1	A
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 4.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	35	42	m $\Omega$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa253</p>
2	S	source		
3	D	drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV45EN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

## 7. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMV45EN2	%K9

[1] % = placeholder for manufacturing site code

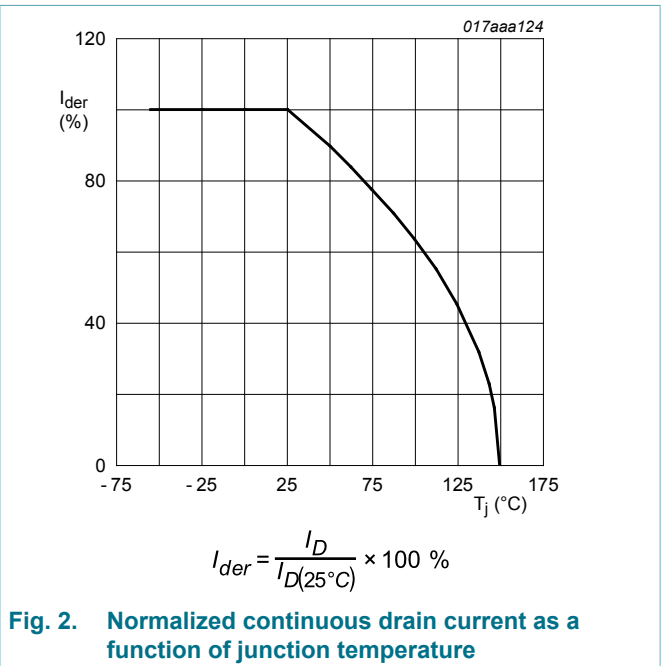
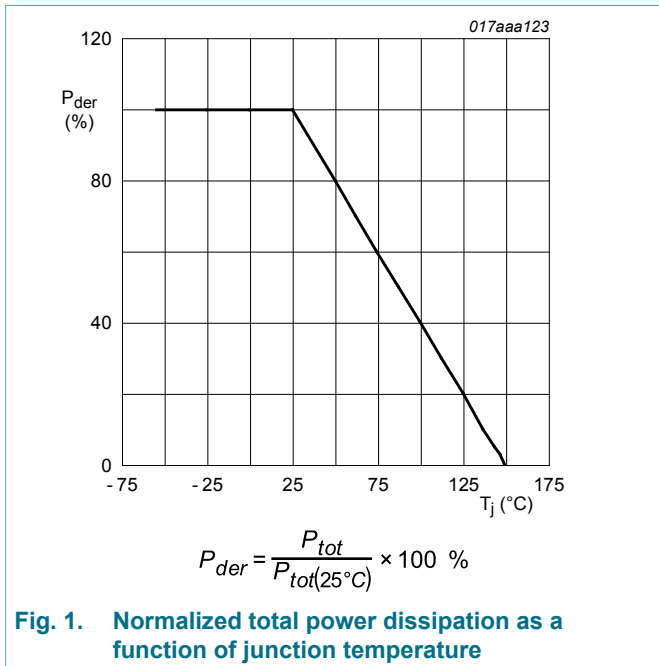
## 8. Limiting values

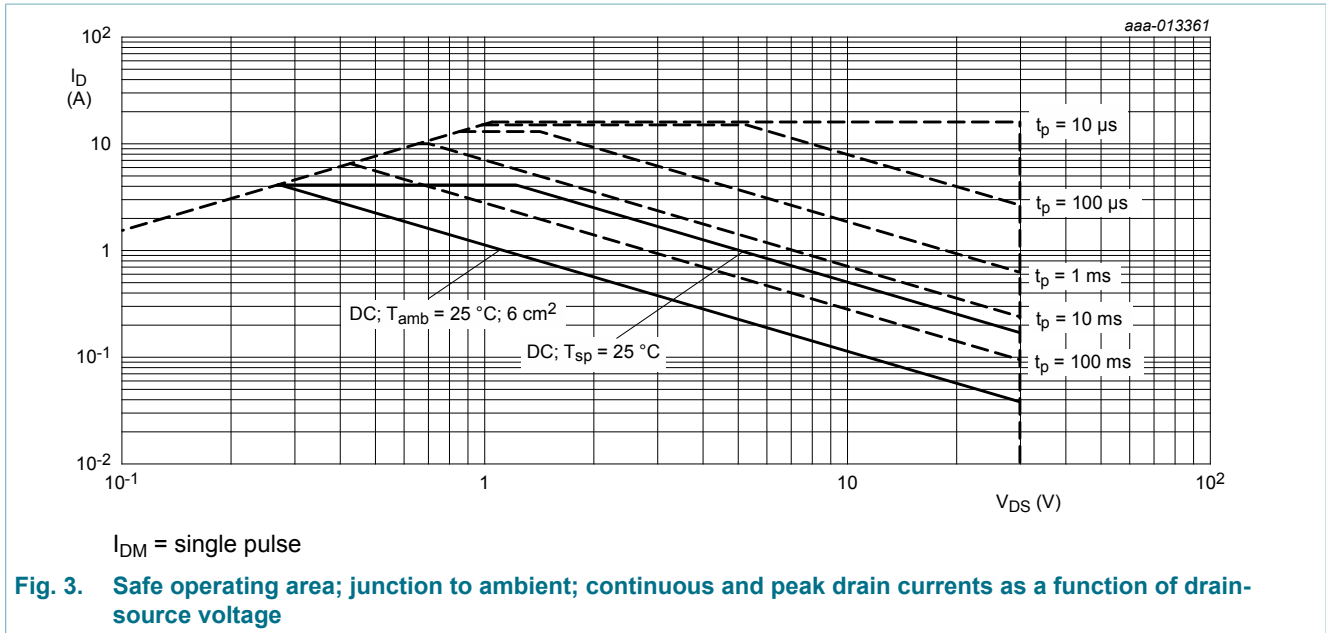
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	5.1	A
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	4.1	A
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	2.6	A
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	16	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	510	mW
			[1]	-	1115	mW
		T <sub>sp</sub> = 25 °C		-	5000	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	209	246	K/W
			[2]	-	95	112	K/W
		in free air; $t \leq 5$ s	[2]	-	62	73	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	20	25	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $6 \text{ cm}^2$ .

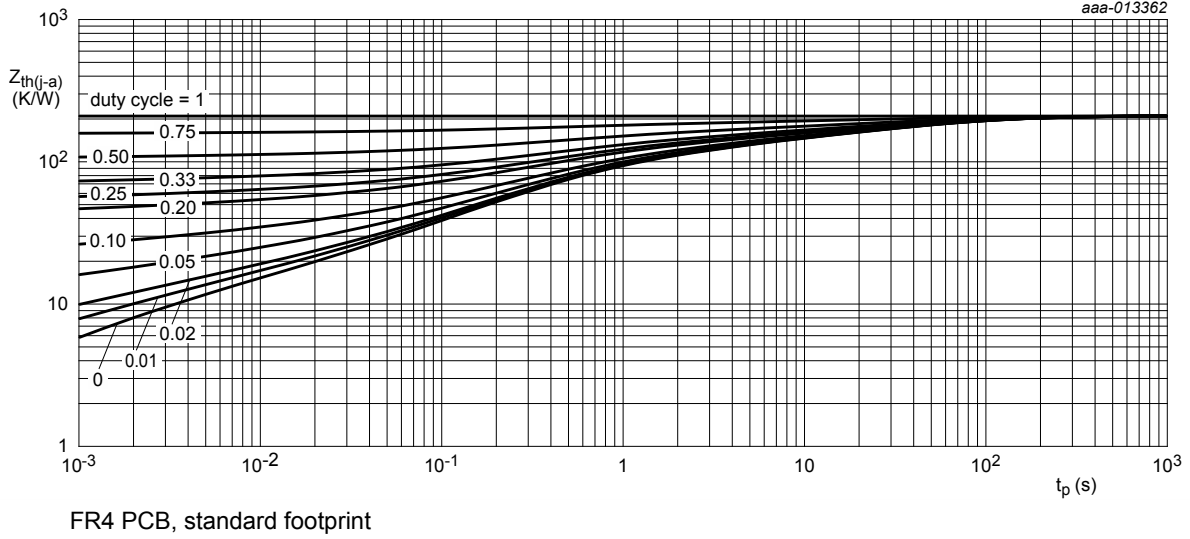


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

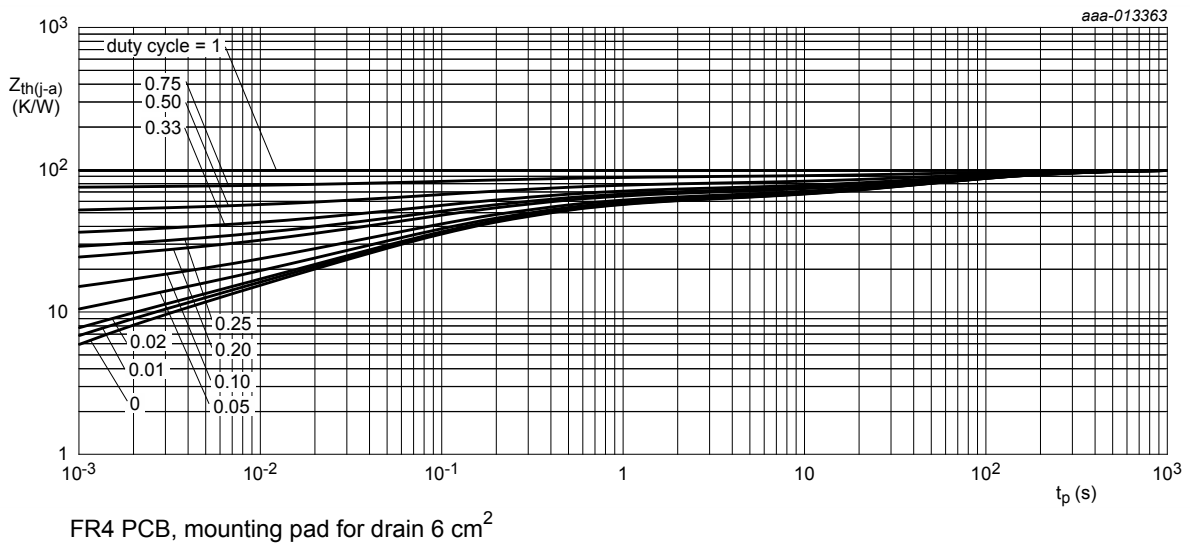
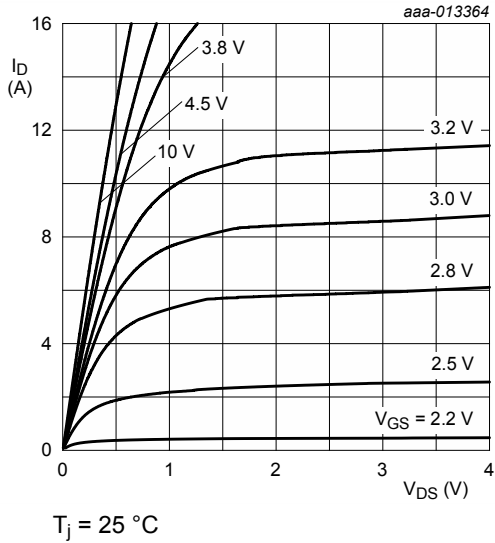


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

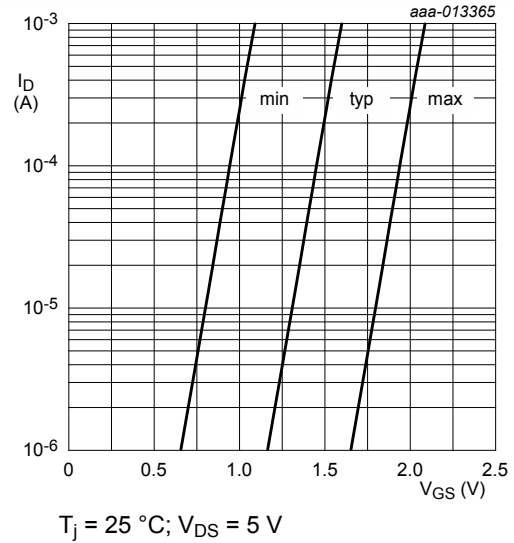
## 10. Characteristics

Table 7. Characteristics

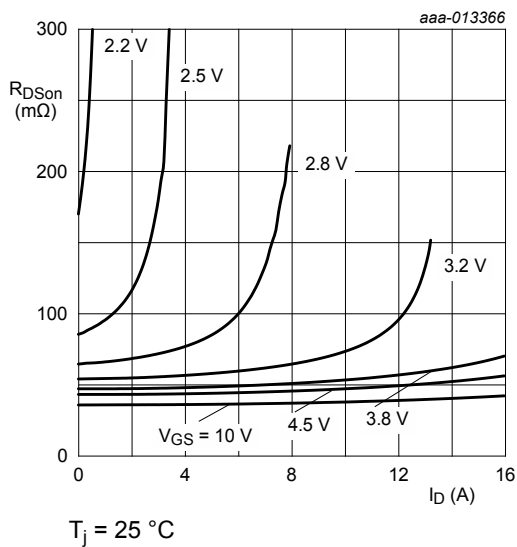
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1	1.5	2	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 4.1 A; T_j = 25 \text{ }^\circ C$	-	35	42	m $\Omega$
		$V_{GS} = 10 V; I_D = 4.1 A; T_j = 150 \text{ }^\circ C$	-	55	66	m $\Omega$
		$V_{GS} = 4.5 V; I_D = 3.6 A; T_j = 25 \text{ }^\circ C$	-	43	54	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10 V; I_D = 2 A; T_j = 25 \text{ }^\circ C$	-	13	-	S
$R_G$	gate resistance	$T_j = 25 \text{ }^\circ C; f = 1 \text{ MHz}$	-	2.3	-	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 15 V; I_D = 3.2 A; V_{GS} = 10 V; T_j = 25 \text{ }^\circ C$	-	3.6	6.3	nC
$Q_{GS}$	gate-source charge		-	0.5	-	nC
$Q_{GD}$	gate-drain charge		-	0.4	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 15 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	209	-	pF
$C_{oss}$	output capacitance		-	50	-	pF
$C_{rss}$	reverse transfer capacitance		-	17	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 V; I_D = 3.2 A; V_{GS} = 10 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	3	-	ns
$t_r$	rise time		-	12	-	ns
$t_{d(off)}$	turn-off delay time		-	11	-	ns
$t_f$	fall time		-	2	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 1 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.8	1.2	V



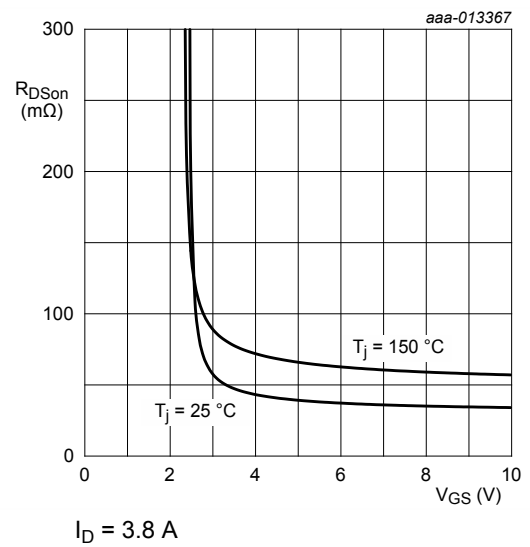
**Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



**Fig. 7. Sub-threshold drain current as a function of gate-source voltage**

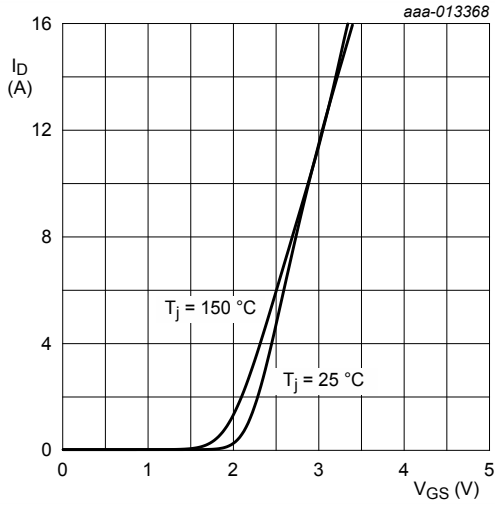


**Fig. 8. Drain-source on-state resistance as a function of drain current; typical values**



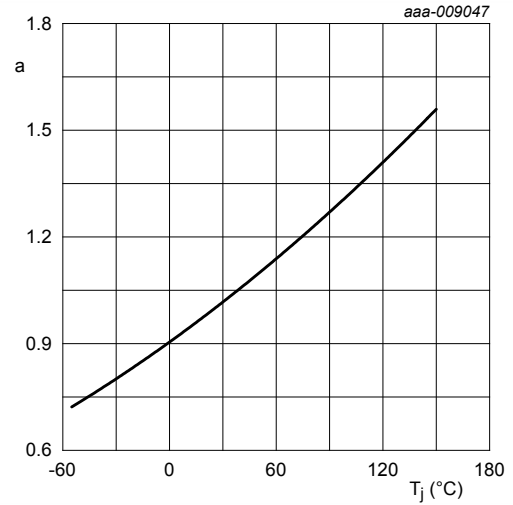
**Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**





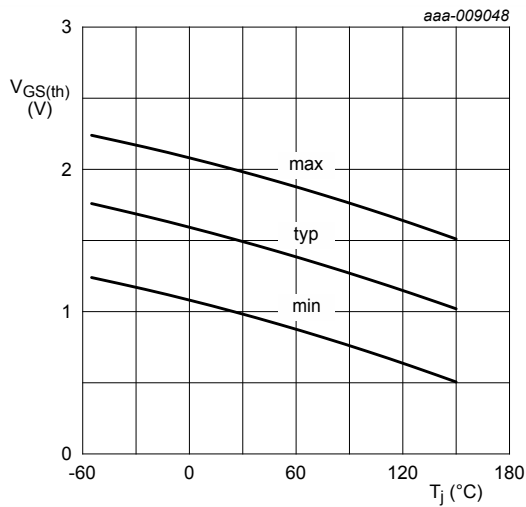
$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



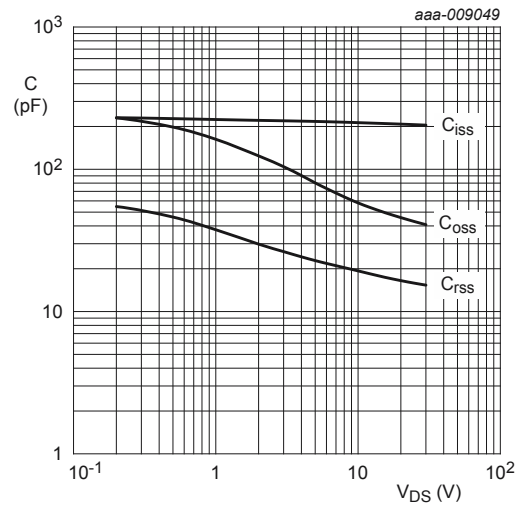
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



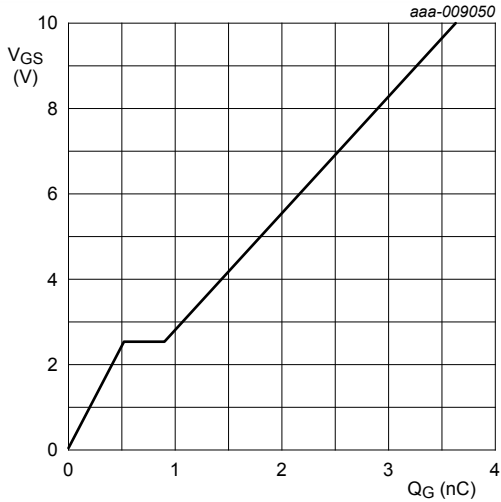
$$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 3.2 \text{ A}; V_{DS} = 15 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

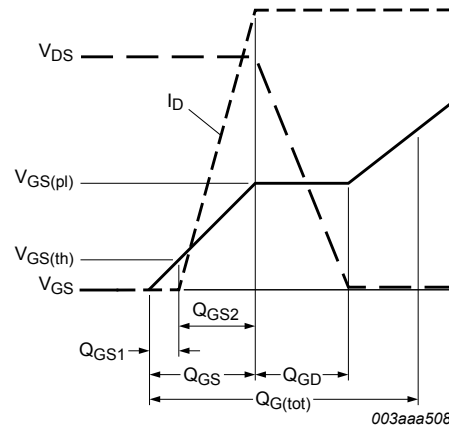
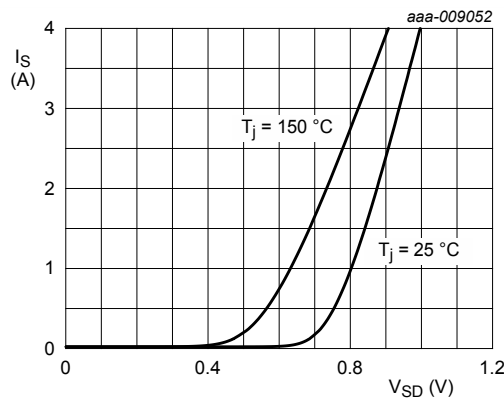


Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

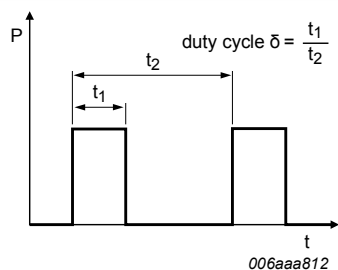
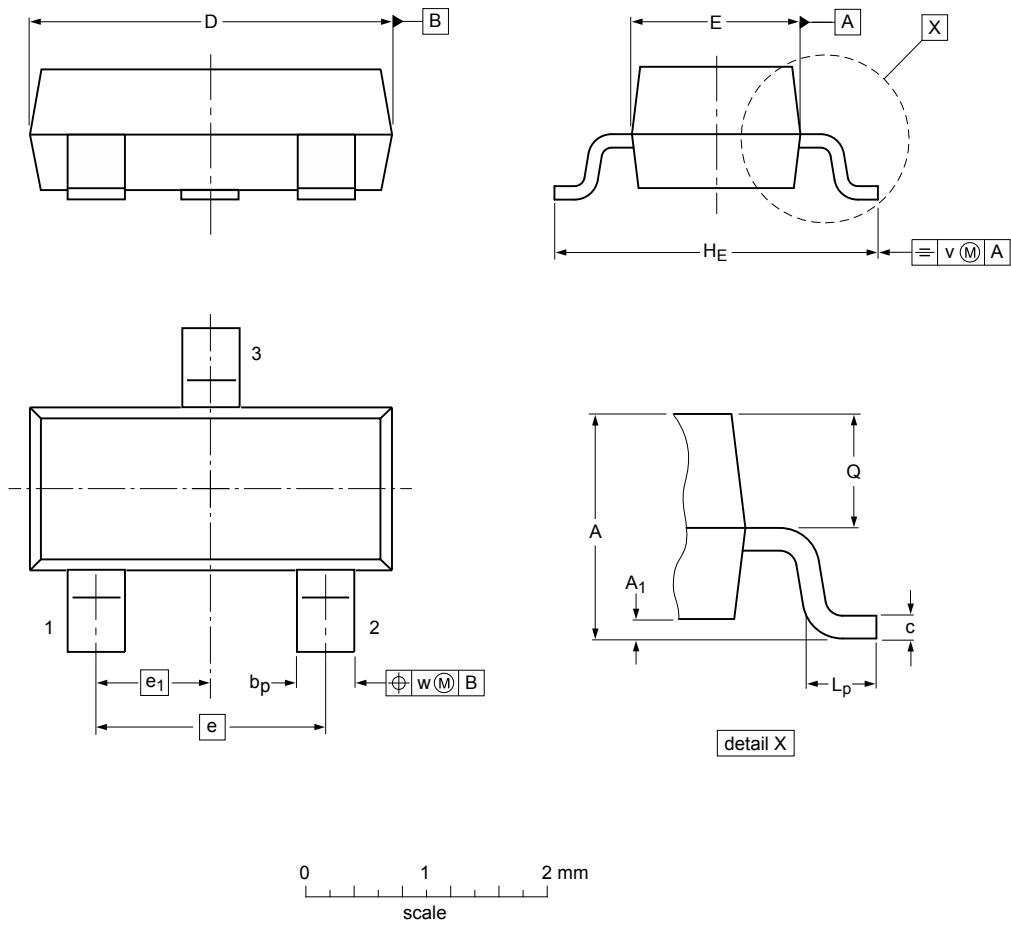


Fig. 17. Duty cycle definition

## 12. Package outline

Plastic surface-mounted package; 3 leads

SOT23



Dimensions (mm are the original dimensions)

Unit	A	A <sub>1</sub>	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
max	1.1	0.1	0.48	0.15	3.0	1.4			2.5	0.45	0.55		
nom							1.9	0.95				0.2	0.1
min	0.9		0.38	0.09	2.8	1.2			2.1	0.15	0.45		

sot023\_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOT23		TO-236AB			-14-06-19 14-09-22

Fig. 18. Package outline TO-236AB (SOT23)

### 13. Soldering

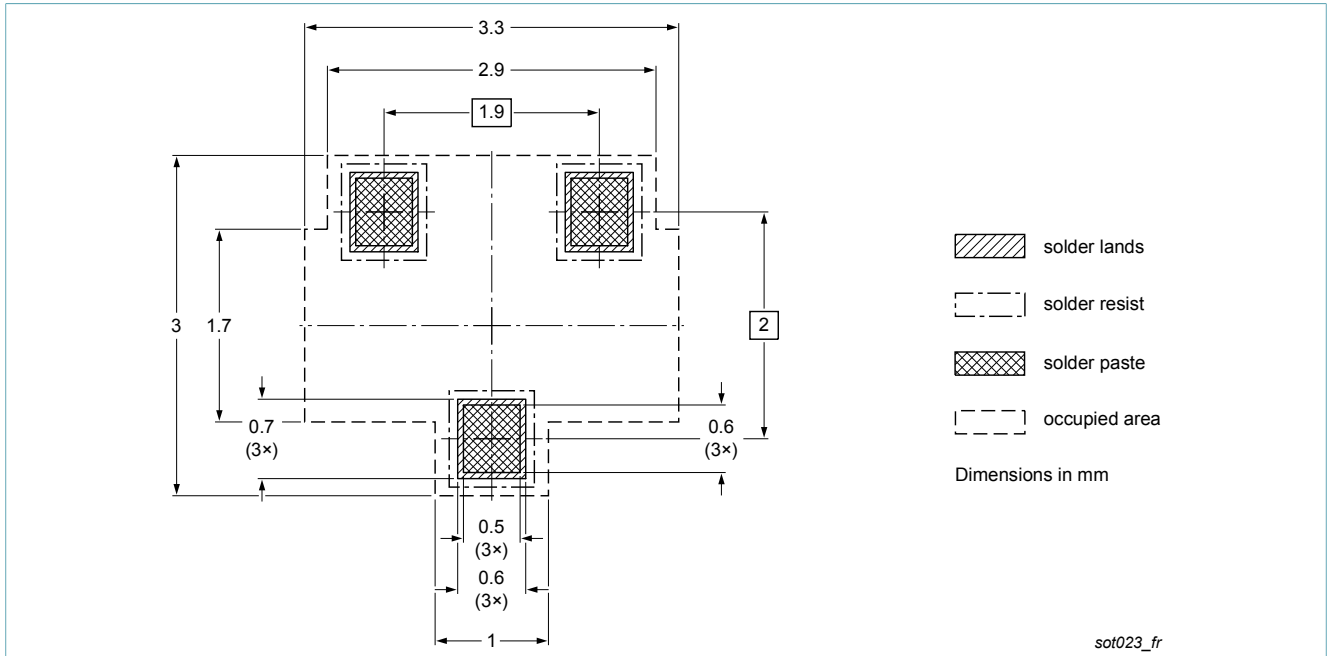


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

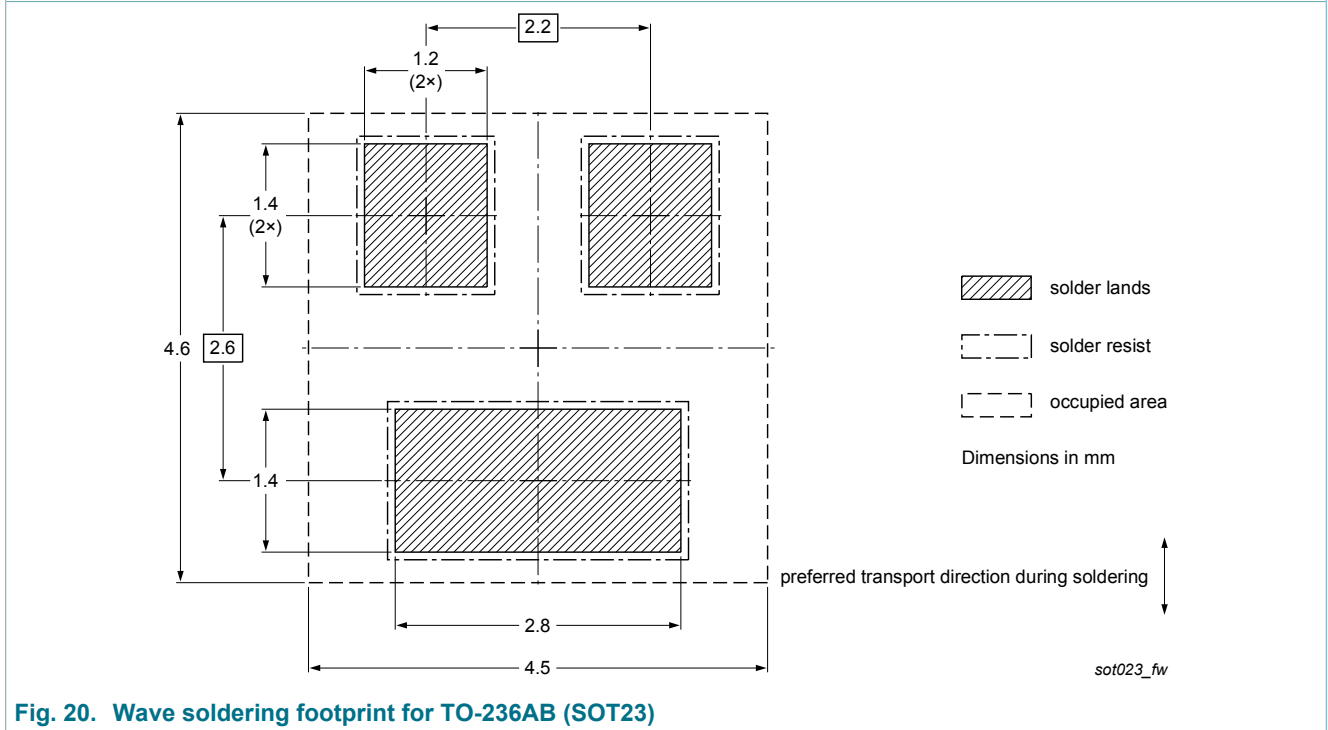


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV45EN2 v.2	20170110	Product data sheet	-	PMV45EN2 v.1
Modifications:	<ul style="list-style-type: none"><li>Section 10. Characteristics: values for forward transconductance and gate resistance changed</li></ul>			
PMV45EN2 v.1	20140603	Product data sheet	-	-

## 15. Legal information

### Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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